

`mos_level3_p.ece`

Description

`mos_level3_p.ece` is a SPICE “level 3” model for a *p*-channel MOS transistor. The real parameters have the same meaning as in the level 3 model implemented in SPICE 3.

The source, drain, gate, and bulk currents are made available as output variables `i_s`, `i_d`, `i_g`, and `i_b`, respectively. The power absorbed by the transistor is made available as `pwr_elec`.

AC (small-signal) implementation of the model is also incorporated, following SPICE 3.